# MICROWAVE POWER GaN HEMT TGI6472-120L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

·BROAD BAND INTERNALLY MATCHED HEMT ·HIGH POWER

Pout= 51.0dBm at Pin= 44dBm

#### ·HIGH GAIN

GL= 11.5dB at Pin= 20dBm

### **·LOW INTERMODULATION DISTORTION**

IM3(MIN.) = -25dBc at Pout= 44dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V IDSset= 4.0A f= 6.4 to 7.2GHz @Pin= 44dBm	dBm	50.0	51.0	_
Drain Current	IDS1		А		11.0	12.0
Power Added Efficiency	ηadd		%		38	
Linear Gain	GL	@Pin= 20dBm	dB	10.5	11.5	
Gain flatness	ΔG		dB			±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 44dBm, ∆f= 5MHz	dBc	-25	-28	
Drain Current	IDS2	(Single Carrier Level)	А			8.0
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin – Pout) × Rth(c-c)	°C		120	140

## **RF PERFORMANCE SPECIFICATIONS** (Ta= 25°C)

Recommended Gate Resistance(Rg): 28 Ω

## ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 46mA	V	-2.0	-4.0	-6.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	А	_	28	_
Gate-Source Breakdown Voltage	VGSO	IGS= -20mA	V	-10		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		0.6	0.8

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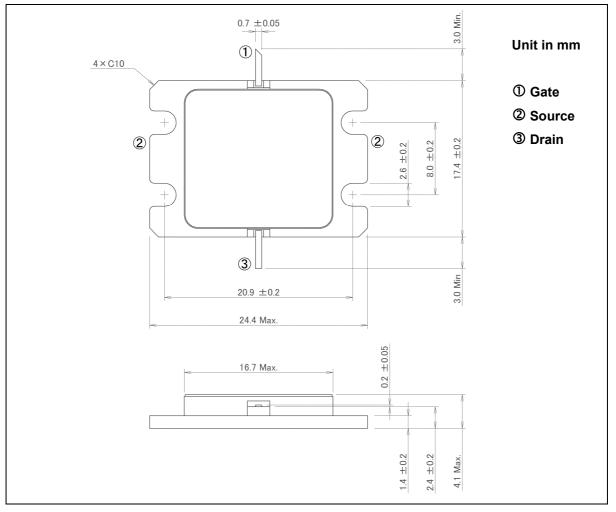
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# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

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CHARACTERISTICS	SYMBOL UN		RATING			
Drain-Source Voltage	VDS	V	50			
Gate-Source Voltage	VGS	V	-10			
Drain Current	IDS	A	18			
Total Power Dissipation (Tc= 25°C)	PT	W	280			
Channel Temperature	Tch	°C	250			
Storage Temperature	Tstg	°C	-65 to +175			

## PACKAGE OUTLINE (7-AA06A)



## HANDLING PRECAUTIONS FOR PACKAGE MODEL

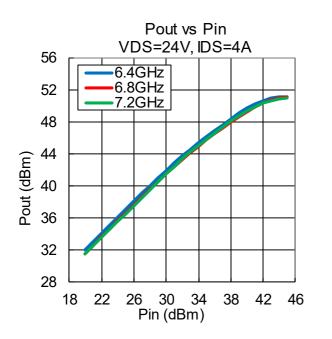
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

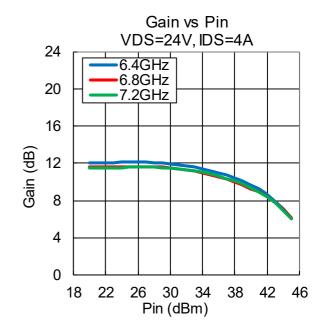
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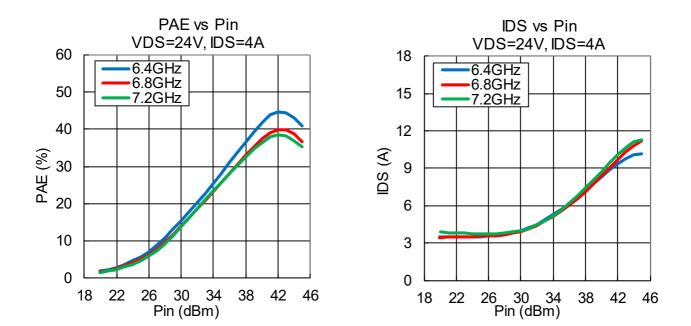
# MICROWAVE SEMICONDUCTOR TECHNICAL DATA

## ·Pout, Gain, PAE, IDS vs. Pin

VDS= 24 V, IDSset= 4.0 A, f= 6.4, 6.8, 7.2 GHz, Ta= +25 °C





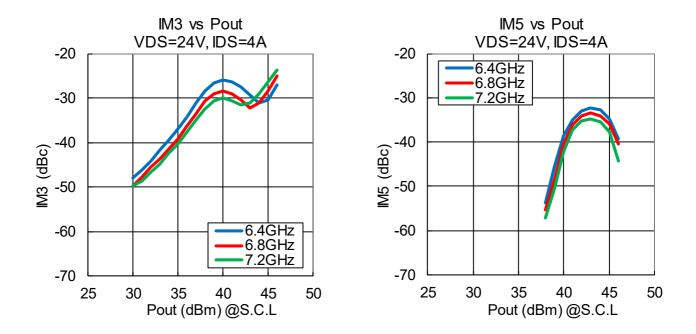


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#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

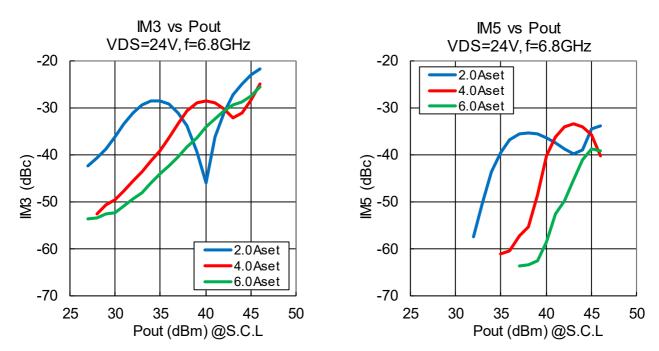
#### ·IM3, IM5 vs. Pout

VDS= 24 V, IDSset= 4.0 A, f= 6.4, 6.8, 7.2 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^\circ C$ 



#### ·IM3, IM5 vs. Pout vs. IDSset

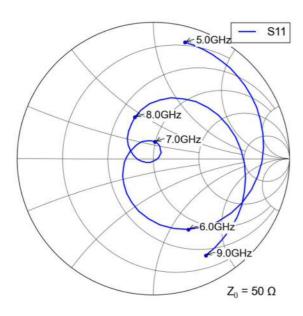
VDS= 24 V, IDSset= 2.0, 4.0, 6.0 A, f= 6.8 GHz, ∆f= 5 MHz, Ta= +25 °C

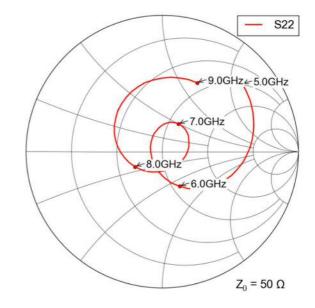


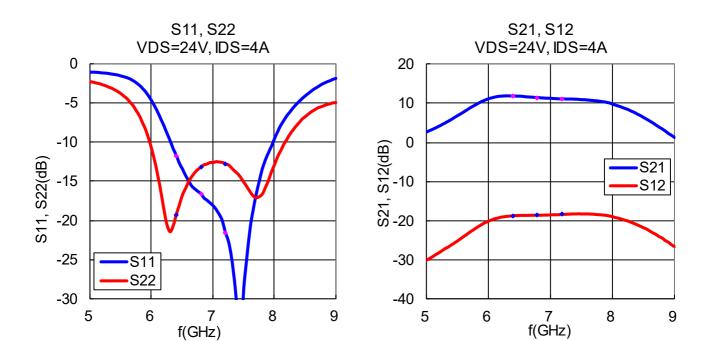
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·S-Parameters

VDS= 24 V, IDSset= 4.0 A, f= =5.0 to 9.0 GHz, Ta= +25 °C







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